

Title (en)

METHOD FOR PRODUCING A SEMICONDUCTOR DIODE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER HALBLEITERDIODE

Title (fr)

PROCEDE DE PRODUCTION D'UNE DIODE A SEMI-CONDUCTEUR

Publication

EP 1208604 A1 20020529 (DE)

Application

EP 00958119 A 20000708

Priority

- DE 0002235 W 20000708
- DE 19938209 A 19990812

Abstract (en)

[origin: DE19938209A1] The invention relates to a semiconductor arrangement and to a method for producing said semiconductor arrangement which enables the current carrying capacity to be improved for set chip dimensions. The inventive semiconductor arrangement comprises trenches (10) made inside the chip, for reducing the power loss or improving the heat dissipation of the chip.

IPC 1-7

H01L 29/861; **H01L 21/329**

IPC 8 full level

H01L 21/329 (2006.01); **H01L 29/861** (2006.01)

CPC (source: EP US)

H01L 29/66136 (2013.01 - EP US); **H01L 29/861** (2013.01 - EP US)

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

US 6716714 B1 20040406; CZ 2002475 A3 20020612; DE 19938209 A1 20010215; DE 19938209 B4 20071227; DE 50013669 D1 20061207; EP 1208604 A1 20020529; EP 1208604 B1 20061025; HU P0202476 A2 20021228; JP 2003507890 A 20030225; JP 4778176 B2 20110921; WO 0113434 A1 20010222

DOCDB simple family (application)

US 4947402 A 20020718; CZ 2002475 A 20000708; DE 0002235 W 20000708; DE 19938209 A 19990812; DE 50013669 T 20000708; EP 00958119 A 20000708; HU P0202476 A 20000708; JP 2001517433 A 20000708